

Joanna L Batstone

List of Publications by Year in descending order

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69
papers

1,628
citations

361045

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40
g-index

69
all docs

69
docs citations

69
times ranked

591
citing authors

#	ARTICLE	IF	CITATIONS
1	Opportunities and Challenges of Global Network Cameras. , 2015, , .		0
2	Kinetic Studies of Nanoscale Crystallization in Electronic Materials. Materials Research Society Symposia Proceedings, 1995, 405, 73.	0.1	0
3	Structural and electronic properties of defects in semiconductors. Proceedings Annual Meeting Electron Microscopy Society of America, 1995, 53, 4-5.	0.0	0
4	Microscopic Processes in Crystallisation. Solid State Phenomena, 1994, 37-38, 257-268.	0.3	17
5	Silicide formation and silicide-mediated crystallization of nickel-implanted amorphous silicon thin films. Journal of Applied Physics, 1993, 73, 8279-8289.	1.1	350
6	<i>In situ</i> crystallization of amorphous silicon in the transmission electron microscope. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1993, 67, 51-72.	0.8	59
7	Stability of visible luminescence from porous silicon. Applied Physics Letters, 1993, 62, 2667-2669.	1.5	36
8	High Resolution In Situ TEM Studies of Silicide-Mediated Crystallization of Amorphous Silicon. Materials Research Society Symposia Proceedings, 1993, 321, 579.	0.1	1
9	In situ transmission electron microscopy studies of silicide-mediated crystallization of amorphous silicon. Applied Physics Letters, 1992, 60, 225-227.	1.5	117
10	Stacking fault asymmetry in epitaxial films of <i>in situ</i> grown ZnSe/GaAs(001). Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1992, 66, 609-620.	0.8	11
11	Degradation of visible cathodoluminescence from porous silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1992, 50, 1372-1373.	0.0	0
12	In situ crystallization of amorphous silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1992, 50, 1346-1347.	0.0	0
13	Dynamic studies of silicide-mediated crystallization of amorphous silicon. Proceedings Annual Meeting Electron Microscopy Society of America, 1992, 50, 1352-1353.	0.0	0
14	The Effect of Rapid Thermal Annealing on Heteroepitaxial Structures. Materials Research Society Symposia Proceedings, 1991, 91, 365.	0.1	4
15	Twin intersections in silicon on sapphire. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1991, 63, 1037-1050.	0.6	11
16	Motion of Crystal/Crystal and Crystal/Amorphous Interfaces. Materials Research Society Symposia Proceedings, 1990, 183, 79.	0.1	0
17	Growth and characterization of ultrathin cobalt silicide films on Si(211) and (311). Journal of Materials Research, 1990, 5, 1032-1041.	1.2	6
18	Interface motion during recrystallization of amorphous NiSi ₂ . Proceedings Annual Meeting Electron Microscopy Society of America, 1990, 48, 524-525.	0.0	1

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19	A crystallographic analysis of the CoSi/Si(111) interface using Transmission Electron Microscopy. Proceedings Annual Meeting Electron Microscopy Society of America, 1990, 48, 574-575.	0.0	0
20	Dependence of the structural and electrical properties of ultrathin cobalt silicide films on formation conditions. Journal of Materials Research, 1989, 4, 144-155.	1.2	16
21	Si _{1-x} CoSi ₂ Structures: Pseudomorphism, Interface Structures, Epitaxial Orientations, and the Control of Pinholes. Journal of the Electrochemical Society, 1989, 136, 815-819.	1.3	22
22	Epitaxial recrystallization and diffusion phenomena in amorphous silicon produced by MeV ion beams. Nuclear Instruments & Methods in Physics Research B, 1989, 37-38, 955-959.	0.6	12
23	Radiation-enhanced diffusion of implanted impurities in amorphous Si. Nuclear Instruments & Methods in Physics Research B, 1989, 39, 343-346.	0.6	7
24	In-situ transmission electron microscopy of NiSi ₂ formation by molecular beam epitaxy. Surface Science, 1989, 208, 317-350.	0.8	47
25	Bonding Configurations at Epitaxial CaF ₂ /Si Interfaces. Materials Research Society Symposia Proceedings, 1989, 139, 351.	0.1	1
26	Reconstruction of (100) Silicon/Disilicide Interfaces. Materials Research Society Symposia Proceedings, 1989, 139, 97.	0.1	2
27	Reconstruction of the NiSi ₂ /Si(100) interface. Proceedings Annual Meeting Electron Microscopy Society of America, 1989, 47, 460-461.	0.0	1
28	Epitaxial films of CoSi ₂ on Si (311) and Si (211). Proceedings Annual Meeting Electron Microscopy Society of America, 1989, 47, 456-457.	0.0	0
29	Origin of A- or B-type NiSi ₂ determined by in situ transmission electron microscopy and diffraction during growth. Physical Review Letters, 1988, 60, 1158-1161.	2.9	50
30	Twin formation and Au segregation during ion beam induced epitaxy of amorphous Si. Applied Physics Letters, 1988, 52, 1043-1045.	1.5	22
31	Control of pinholes in epitaxial CoSi ₂ layers on Si(111). Applied Physics Letters, 1988, 52, 648-650.	1.5	72
32	Trapping of Au in Si during pulsed laser irradiation: A comparison with ion beam induced segregation. Applied Physics Letters, 1988, 53, 2486-2488.	1.5	16
33	Coreless defects and the continuity of epitaxial NiSi ₂ /Si(100) thin films. Applied Physics Letters, 1988, 52, 828-830.	1.5	32
34	Evidence for the influence of interfacial atomic structure on electrical properties at the epitaxial CaF ₂ /Si(111) interface. Physical Review Letters, 1988, 60, 1394-1397.	2.9	84
35	Control of epitaxial orientation of Si on CoSi ₂ (111). Applied Physics Letters, 1988, 52, 1611-1613.	1.5	48
36	Batstone and Phillips Reply. Physical Review Letters, 1988, 61, 2275-2275.	2.9	11

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37	Nonequilibrium segregation and trapping phenomena during ion-induced crystallization of amorphous Si. Physical Review Letters, 1988, 60, 1322-1325.	2.9	49
38	Radiation-enhanced diffusion of Au in amorphous Si. Applied Physics Letters, 1988, 52, 1213-1215.	1.5	38
39	Segregation and Trapping of Gold During Ion-Induced Crystallization of Amorphous Si. Materials Research Society Symposia Proceedings, 1988, 100, 399.	0.1	1
40	Diffusion of Au in Amorphous Si During Ion-Beam Irradiation. Materials Research Society Symposia Proceedings, 1988, 100, 87.	0.1	1
41	New Directions in the Growth of Epitaxial Insulators and Metals on Silicon. Materials Research Society Symposia Proceedings, 1988, 116, 403.	0.1	2
42	Growth of Thin Epitaxial CoSi_2 Layers on Si(100). Materials Research Society Symposia Proceedings, 1988, 116, 439.	0.1	25
43	The Effect of Rapid Thermal Annealing on the Dislocation Structure of Silicon on Sapphire. Materials Research Society Symposia Proceedings, 1988, 138, 373.	0.1	10
44	TEM and cathodoluminescence of precipitates in II-VI semiconductors. Proceedings Annual Meeting Electron Microscopy Society of America, 1988, 46, 488-489.	0.0	0
45	Subboundary-free zone-melt recrystallization of thin-film silicon. Applied Physics Letters, 1987, 51, 1256-1258.	1.5	42
46	Mechanisms of buried oxide formation by ion implantation. Applied Physics Letters, 1987, 50, 19-21.	1.5	77
47	Nucleation and Growth of Ultrathin Epitaxial Metal Silicides on Silicon. Materials Research Society Symposia Proceedings, 1987, 102, 253.	0.1	0
48	Ultrathin Single Crystal CoSi_2 Layers on Si(111) and Si(100). Materials Research Society Symposia Proceedings, 1987, 102, 265.	0.1	10
49	In-Situ Rapid Thermal Annealing of Heterostructures Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1987, 102, 355.	0.1	2
50	Hot Electron Transistors Using Si/ CoSi_2 . Materials Research Society Symposia Proceedings, 1987, 102, 361.	0.1	6
51	The Effect of Formation Conditions on the Structural and Electrical Properties of Ultrathin Cobalt Silicide Films. Materials Research Society Symposia Proceedings, 1987, 102, 389.	0.1	1
52	Effect of Atomic Structure at the Epitaxial CaF_2 /Si(111) Interface on Electrical Properties. Materials Research Society Symposia Proceedings, 1987, 102, 45.	0.1	3
53	In-Situ Rapid Thermal Annealing of Heterostructures Grown by Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 1987, 107, 253.	0.1	0
54	Hot Electron Transistors Using Si/ CoSi_2 . Materials Research Society Symposia Proceedings, 1987, 107, 259.	0.1	7

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55	Techniques of Insulator/Semiconductor Heterostructure Specimen Preparation. Materials Research Society Symposia Proceedings, 1987, 115, 63.	0.1	5
56	Electrical Transport in Ultrathin Films of CoSi_2 on Si(111). Materials Research Society Symposia Proceedings, 1987, 91, 427.	0.1	2
57	Characterization of Ultrathin CoSi_2 on Si(111) Layers.. Materials Research Society Symposia Proceedings, 1987, 91, 445.	0.1	15
58	In-Situ Studies of the MBE Growth of CoSi_2 on Si (111) in a UHV Transmission Electron Microscope. Materials Research Society Symposia Proceedings, 1987, 94, 151.	0.1	0
59	In situ study of the molecular beam epitaxy of CoSi_2 on (111) $\text{\AA}^{\circ}\text{Si}$ by transmission electron microscopy and diffraction. Applied Physics Letters, 1987, 51, 45-47.	1.5	81
60	Electrical and structural characterization of ultrathin epitaxial CoSi_2 on Si(111). Applied Physics Letters, 1987, 51, 1895-1897.	1.5	51
61	Rapid thermal processing to improve the epitaxy of (100) $\text{\AA}^{\circ}\text{silicon}$ on (111,02) sapphire. Applied Physics Letters, 1987, 50, 466-468.	1.5	15
62	High-resolution electron microscopy of interfaces and surfaces. Ultramicroscopy, 1987, 22, 35-46.	0.8	17
63	The Role of Implant Temperature in the Formation of Thin Buried Oxide Layers. Materials Research Society Symposia Proceedings, 1986, 74, 585.	0.1	4
64	Microstructural Characterization of High Dose Oxygen Implanted Silicon. Materials Research Society Symposia Proceedings, 1986, 74, 597.	0.1	3
65	Electron Transport Through Epitaxial Metal/Semiconductor Heterostructures. Materials Research Society Symposia Proceedings, 1986, 77, 271.	0.1	4
66	Correlation of Electrical Properties with Structure Imaging of Semiconductor Interfaces. Materials Research Society Symposia Proceedings, 1986, 82, 335.	0.1	3
67	Dislocation Luminescence in ZnSe. Proceedings Annual Meeting Electron Microscopy Society of America, 1986, 44, 818-819.	0.0	2
68	Atomic structure imaging of the Si/SiO_2 interface with high-resolution electron microscopy. Proceedings Annual Meeting Electron Microscopy Society of America, 1986, 44, 390-391.	0.0	2
69	Luminescence studies of individual dislocations in II-VI (ZnSe) and III-V (InP) semiconductors. Journal of Physics C: Solid State Physics, 1984, 17, 6477-6492.	1.5	94